	Hits	Search Text	DB	Time stamp
4	2512	((atomic adj layer adj (epitaxy	USPAT;	2003/09/21 20:17
		deposition) ald (sequential digital) adj	US-PGPUB	
6	12	(CVD chemical adj vapor adj deposition)))	HCDAM.	2003/09/21 20:17
0	12	((((atomic adj layer adj (epitaxy deposition) ald (sequential digital) adj	USPAT; US-PGPUB	2003/09/21 20:17
	j	(CVD chemical adj vapor adj deposition)))	US-FGFUD	
		) and nanolaminate) and silicide		
5	38	(((atomic adj layer adj (epitaxy	USPAT;	2003/09/21 20:42
3	30	(((atomic ad) layer ad) (epitaxy   deposition) ald (sequential digital) adj	US-PGPUB	2003/09/21 20:42
		(CVD chemical adj vapor adj deposition)))	US-FGFUD	
		) and nanolaminate		
.7	1	,	USPAT;	2003/09/21 20:39
'	-	indiotamento with billotte	US-PGPUB	2003,03,21 20.33
8	1	("6287635").PN.	USPAT;	2003/09/21 20:36
_		,, ,	US-PGPUB	2010, 00, 22 2010
9	0	nanolaminate with WSi\$	USPAT;	2003/09/21 20:40
	-		US-PGPUB	
10	1	nanolaminate same (WSi\$ silicide)	USPAT;	2003/09/21 20:37
		()	US-PGPUB	2000, 03, 22 20.0
11	1	09/954705.app.	USPAT;	2003/09/21 20:39
			US-PGPUB	
12	65	nanolaminate	USPAT;	2003/09/21 20:40
			US-PGPUB	
-	3606	(427/250-253,255.18,255.17,255.23,255.26,25		25603929256.39343dcls.
			US-PGPUB	
	146	((427/250-253,255.18,255.17,255.23,255.26,2	55/S27AT255.31	,2863392/28513937.CCLS.)
		and tungsten with silicide	US-PGPUB	
-	3	(((427/250-253,255.18,255.17,255.23,255.26,	255 PAT; 255.3	12063/09220557393) .CCLS.
		and tungsten with silicide) and (atomic	US-PGPUB	
-	4	4dj42av2b0a253d2p5s18j2b5o17A2b5.23,255.26,	255 PAT; 255.3	12065/09220557392) .CCLS.
		and tungsten with silicide) and (atomic	US-PGPUB	
-	4867	44271248r1a250d253s255oh8o25ALDy,255.23,255	206P255.27,2	52003/29523927252.393).c
			US-PGPUB	
-	57	((427/248.1,250-253,255.18,255.17,255.23,25	5 USGAI55.27,	28603102520398;025.393).
		and (atomic adj layer adj deposition or	US-PGPUB	
-	5	ALD#27/248.1,250-253,255.18,255.17,255.23,2		,2663309286.3829255.393)
		and (atomic adj layer adj deposition or	US-PGPUB	
_	0	ADD0\$2896.appgsten with silicide	USPAT;	2003/09/20 17:14
1	1705	separate and leaves and describe as man	US-PGPUB	0000 (00 (00 17 17
_	1705	atomic adj layer adj deposition or ALD	USPAT;	2003/09/20 17:17
_	90	(atomic add layer add denocition or AID)	US-PGPUB	2002/00/20 17 25
_	90	(atomic adj layer adj deposition or ALD)	USPAT;	2003/09/20 17:35
_	89	and tungsten with silicide (atomic adj layer adj deposition or ALD)	US-PGPUB	2003/00/20 10:02
. [	0,5	and WSi\$7	USPAT;	2003/09/20 18:02
	58	((atomic adj layer adj deposition or ALD)	US-PGPUB USPAT;	2003/09/20 17:36
	30	and WSi\$7) not ((atomic adj layer adj	US-PGPUB	2003/09/20 17:30
		deposition or ALD) and tungsten with	US-FGFUB	
		silicide)		
_	. 0	(((atomic adj layer adj deposition or ALD)	USPAT;	2003/09/20 17:36
	J	and WSi\$7) not ((atomic adj layer adj	US-PGPUB	1200,05,20 1,.50
		deposition or ALD) and tungsten with	12 23102	
		silicide)) and @ad<=2001020		
/				2002/00/20 10 15
_	14	(((atomic adj laver adj deposition or ALD)	USPAT:	1 2003/09/20 19:15 1
-	14	(((atomic adj layer adj deposition or ALD) and WSi\$7) not ((atomic adj layer adj	USPAT; US-PGPUB	2003/09/20 19:15
_	14	and WSi\$7) not ((atomic adj layer adj	USPAT; US-PGPUB	2003/09/20 19:15
-	14	(((atomic adj layer adj deposition or ALD) and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020		2003/09/20 19:15
-	14 71	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with		2003/09/20 19:15
-	71	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.	US-PGPUB	
- -		and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.	US-PGPUB USPAT;	
-	71	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.  ((427/255.392).CCLS.) and (atomic adj layer adj deposition ald (sequential	US-PGPUB USPAT; US-PGPUB	2003/09/20 17:43
- -	71	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.  ((427/255.392).CCLS.) and (atomic adj layer adj deposition ald (sequential digital) adj (CVD chemical adj vapor adj	US-PGPUB USPAT; US-PGPUB USPAT;	2003/09/20 17:43
- -	71 5	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.  ((427/255.392).CCLS.) and (atomic adj layer adj deposition ald (sequential digital) adj (CVD chemical adj vapor adj deposition))	US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2003/09/20 17:43
	71	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.  ((427/255.392).CCLS.) and (atomic adj layer adj deposition ald (sequential digital) adj (CVD chemical adj vapor adj deposition)) ((427/255.392).CCLS.) and (atomic adj	US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2003/09/20 17:43
-	71 5	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.  ((427/255.392).CCLS.) and (atomic adj layer adj deposition ald (sequential digital) adj (CVD chemical adj vapor adj deposition)) ((427/255.392).CCLS.) and (atomic adj layer adj epitaxy ale)	US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2003/09/20 17:43 2003/09/20 19:12 2003/09/20 18:01
- ,	71 5	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.  ((427/255.392).CCLS.) and (atomic adj layer adj deposition ald (sequential digital) adj (CVD chemical adj vapor adj deposition)) ((427/255.392).CCLS.) and (atomic adj layer adj epitaxy ale) ((427/248.1,250-253,255.18,255.17,255.23,255.	US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB 50280A255.27,	2003/09/20 17:43 2003/09/20 19:12 2003/09/20 18:01
- ,	71 5 2 58	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.  ((427/255.392).CCLS.) and (atomic adj layer adj deposition ald (sequential digital) adj (CVD chemical adj vapor adj deposition)) ((427/255.392).CCLS.) and (atomic adj layer adj epitaxy ale) ((427/248.1,250-253,255.18,255.17,255.23,25 and (atomic adj layer adj epitaxy or ALE)	US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2003/09/20 17:43 2003/09/20 19:12 2003/09/20 18:01 28603102530392;035.393).0
- ,	71 5	and WSi\$7) not ((atomic adj layer adj deposition or ALD) and tungsten with silicide)) and @ad<=20001020 (427/255.392).CCLS.  ((427/255.392).CCLS.) and (atomic adj layer adj deposition ald (sequential digital) adj (CVD chemical adj vapor adj deposition)) ((427/255.392).CCLS.) and (atomic adj layer adj epitaxy ale) ((427/248.1,250-253,255.18,255.17,255.23,255.	US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	2003/09/20 17:43 2003/09/20 19:12 2003/09/20 18:01 28603102530392;035.393).0

-	1	(((427/248.1,250-253,255.18,255.17,255.23,2		,2663309286.8829255.393
_	2512	and (atomic adj layer adj epitaxy or ALE))	US-PGPUB .	2002/00/20 20-11
-	2312	andomingadinlwyeh adjicepetaxy deposition) ald (sequential digital) adj (CVD chemical	USPAT; US-PGPUB	2003/09/20 20:11
		adj vapor adj deposition))	US-FGFUB	
-	. 0		USPAT;	2003/09/21 20:16
		deposition) ald (sequential digital) adj	US-PGPUB	2000, 03, 21 20.10
		(CVD chemical adj vapor adj deposition)))		
1		and hydrate with substrate		
-	1	((atomic adj layer adj (epitaxy	USPAT;	2003/09/20 19:15
		deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition))) and hydrated with substrate		
_	130		USPAT;	2003/09/20 20:50
İ	150	deposition) ald (sequential digital) adj	US-PGPUB	2003/03/20 20:30
A <sub>so</sub>		(CVD chemical adj vapor adj deposition)))	10102	
		and atomic with hydrogen		
-	22	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2003/09/20 19:43
		deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition)))		
		and atomic with hydrogen) and @ad<=20001020) and (silicide tungsten		
		titanium)		1
-	65	· ·	USPAT;	2003/09/20 19:42
		deposition) ald (sequential digital) adj	US-PGPUB	2000, 03, 20 23.12
	+	(CVD chemical adj vapor adj deposition)))		
		and atomic adj hydrogen		
_	49	1 ( (	USPAT;	2003/09/20 19:43
		deposition) ald (sequential digital) adj (CVD chemical adj vapor adj deposition)))	US-PGPUB	
		and atomic adj hydrogen) and (silicide	1	
		tungsten titanium)		
-	14	((((atomic adj layer adj (epitaxy	USPAT;	2003/09/20 19:50
	7.4	deposition) ald (sequential digital) adj	US-PGPUB	
		(CVD chemical adj vapor adj deposition)))		
		and atomic adj hydrogen) and (silicide tungsten titanium)) and @ad<=20001020		
-	1209		USPAT;	2003/09/20 19:50
	1203	chloride halogen halide)	US-PGPUB	2003/03/20 19.30
-	3	(hydrogen with reduce with (chlorine	USPAT;	2003/09/20 20:00
		chloride halogen halide)) and (atomic adj	US-PGPUB	1
		layer adj (epitaxy deposition) ald		
		(sequential digital) adj (CVD chemical adj vapor adj deposition))		H
_	100		USPAT;	2003/09/20 20:01
			US-PGPUB	2003/03/20 20.01
-	85	(hydrogen with scavenge with chlori?e) and	USPAT;	2003/09/20 20:01
		@ad<=20001020	US-PGPUB	
-	3	((hydrogen with scavenge with chlori?e)	USPAT;	2003/09/20 20:03
_	4	and @ad<=20001020) and silicide	US-PGPUB	2002/00/00 00 01
	4	((hydrogen with scavenge with chlori?e) and @ad<=20001020) and tungsten	USPAT; US-PGPUB	2003/09/20 20:04
_	2	((hydrogen with scavenge with chlori?e)	USPAT;	2003/09/20 20:05
		and @ad<=20001020) and (CVD ALD atomic adj	US-PGPUB	2003/03/20 20.03
		layer adj (deposition epitaxy) chemical		
		adj vapor adj deposition)		
7	48		USPAT;	2003/09/20 20:12
		deposition) ald (sequential digital) adj (CVD chemical adj vapor adj deposition)))	US-PGPUB	
		and tungsten adj layer		
_	25		USPAT;	2003/09/20 20:12
		deposition) ald (sequential digital) adj	US-PGPUB	2000/05/20 20.12
		(CVD chemical adj vapor adj deposition)))		
	4-	and tungsten adj layer) and hydrogen		
-	45	( ( ( ) constraints of the constraints	USPAT;	2003/09/20 20:50
		deposition) ald (sequential digital) adj   (CVD chemical adj vapor adj deposition)))	US-PGPUB	
		and atomic with hydrogen) and		
		@ad<=20001020		

-	65	((atomic adj layer adj (epitaxy	USPAT;	2003/09/20 20:50
		deposition) ald (sequential digital) adj	US-PGPUB	
İ		(CVD chemical adj vapor adj deposition)))		
		and atomic adj hydrogen	1	